arXiv:cond-mat/0409065v1 [cond-mat.mes-hall] 3 Sep 2004

Microwave strengths to induce magnetoresistance oscillations in high-mobility 2DES in a photon-assisted impurity scattering model

X.L. Lei
Department of Physics, Shanghai Jiaotong University, 1954 Huashan Rd., Shanghai 200030, China

(February 2, 2008)

Although the major feature (such as period and phase) of the microwave-induced magnetoresistance oscillations in two-dimensional (2D) electron systems is insensitive to the behavior of the elastic scattering in the photon-assisted impurity scattering model,[1] the required microwave intensity to induce an effective oscillation depends strongly on the form of the impurity potential. We present here the calculated results of the longitudinal resistivity R_{xx} versus ω/ω_c (ω_c is the cyclotron frequency) of 2D electrons at lattice temperature $T = 1\,\mathrm{K}$ subjected to microwave irradiations of frequency $\omega/2\pi = 100\,\mathrm{GHz}$ in GaAs-AlGaAs heterojunctions having same carrier density $N_\mathrm{e} = 3\times10^{11}\mathrm{cm}^{-2}$, same zero-magnetic-field linear mobility $\mu_0 = 2.4\times10^7\mathrm{m}^2\mathrm{V}^{-1}\mathrm{s}^{-1}$, and same level broadening parameter $\alpha = 12$, but the elastic scatterings being respectively due to: (a) remote charged impurities located at a distance $s = 60\,\mathrm{nm}$ from the interface (Fig. 1); (b) remote changed impurities at $s = 20\,\mathrm{nm}$ from the interface (Fig. 2); (c) background charged impurities (Fig. 3); (d) short-range (δ-function type) potential (Fig. 4). The microwaves are assumed to be linearly polarized along the same direction as the dc current (x-direction) having different electric field amplitudes E_s as indicated in the figures. It is seen that for inducing a roughly equivalent oscillation the required microwave strength may be an order of magnitude smaller in the case of background impurity scattering than that of remote impurity scattering of $s = 60\,\mathrm{nm}$.

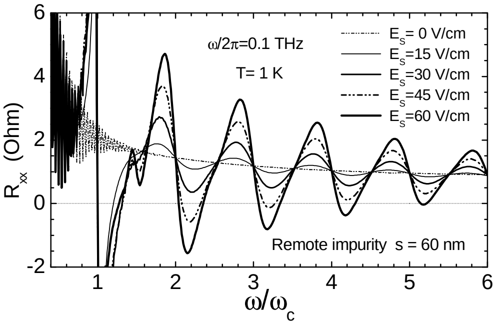

FIG. 1. The longitudinal magnetoresistivity R_{xx} of a GaAs-based 2DEG subjected to a microwave field $E_s\sin(\omega t)$ in the x-direction. The parameters are: temperature $T = 1\,\mathrm{K}$, electron density $N_\mathrm{e} = 3.0\times10^{11}\,\mathrm{cm}^{-2}$, zero-magnetic-field linear mobility $\mu_0 = 2.4\times10^7\,\mathrm{cm}^2\,\mathrm{V}^{-1}\,\mathrm{s}^{-1}$, and the broadening coefficient $\alpha = 12$. The elastic potential is due to remote charged impurities located at a distance $s = 60\,\mathrm{nm}$ from the interface.

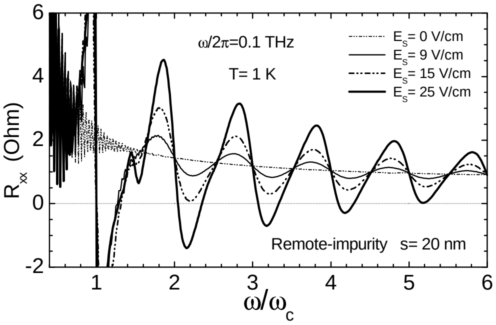

FIG. 2. Remote imputity scattering, $s = 20\,\mathrm{nm}$.

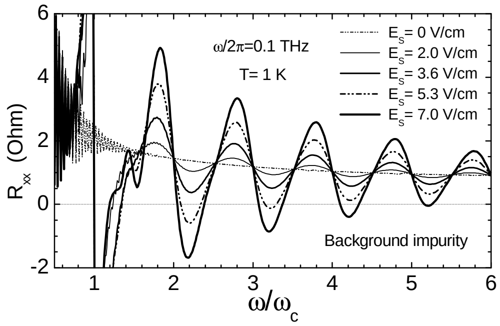

FIG. 3. Background impurity scattering.

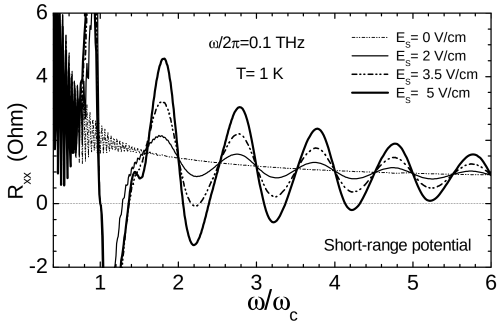

FIG. 4. Short-range potential scattering.

---

[1] X.L. Lei and S.Y. Liu, Phys. Rev. Lett. **91**, 226805 (2003); X.L. Lei, J. Phys.: Cond. Matter **16**, 4045 (2004).